

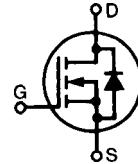
**HiPerFET™ Power MOSFETs
ISOPLUS247™
(Electrically Isolated Back Surface)**

IXFR 44N60

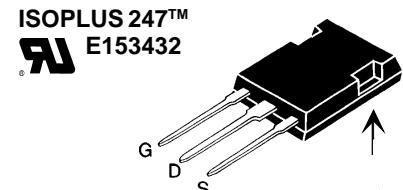
$V_{DSS} = 600$ V
 $I_{D25} = 38$ A
 $R_{DS(on)} = 130$ mΩ

$t_{rr} \leq 250$ ns

Single MOSFET Die



Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600		V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	600		V
V_{GS}	Continuous	± 20		V
V_{GSM}	Transient	± 30		V
I_{D25}	$T_c = 25^\circ\text{C}$	38		A
I_{DM}	$T_c = 25^\circ\text{C}$, Note 1	60		A
I_{AR}	$T_c = 25^\circ\text{C}$	44		A
E_{AR}	$T_c = 25^\circ\text{C}$	60		mJ
E_{AS}	$T_c = 25^\circ\text{C}$	3		J
dv/dt	$I_s \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2\Omega$	5		V/ns
P_D	$T_c = 25^\circ\text{C}$	400		W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	1.6 mm (0.063 in.) from case for 10 s	300		°C
V_{ISOL}	50/60 Hz, RMS $t = 1\text{ min}$	2500		V~
Weight		5		g



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low drain to tab capacitance(<30pF)
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC & DC motor control

Advantages

- Easy assembly
- Space savings
- High power density
- Low noise to ground

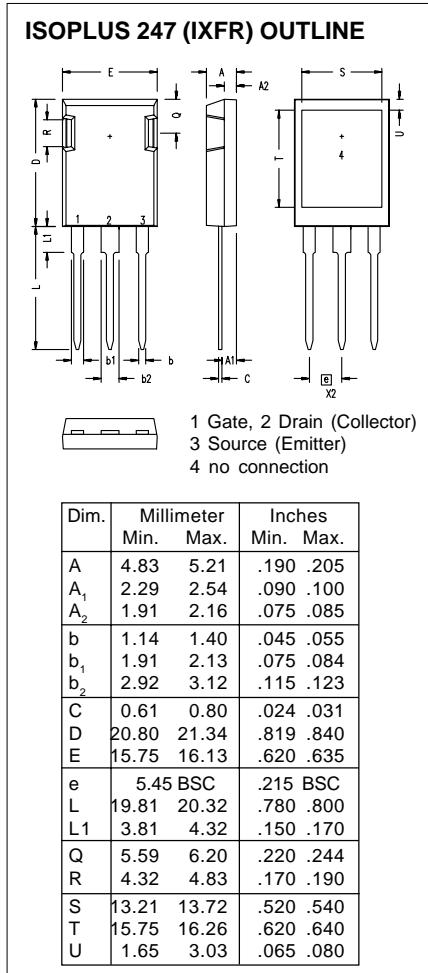
Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 250\mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4\text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = I_T$ Notes 2, 3			130 mΩ

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$V_{DS} = 10 \text{ V}; I_D = I_T$	Notes 2, 3	30	45	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		8900	pF	
			1000	pF	
			330	pF	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ $R_G = 2.0 \Omega$ (External), Notes 2, 3		42	ns	
			55	ns	
			110	ns	
			45	ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_T$ Notes 2, 3		330	nC	
			60	nC	
			65	nC	
R_{thJC}			0.30	K/W	
R_{thCK}			0.15	K/W	

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$			44	A
I_{SM}	Repetitive; Note 1			176	A
V_{SD}	$I_F = I_T, V_{GS} = 0 \text{ V}$, Notes 2, 3			1.3	V
t_{rr} Q_{RM} I_{RM}	$I_F = 50 \text{ A}, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$		250	ns	
			1.4		μC
			8		A

Note: 1. Pulse width limited by T_{JM}
 2. Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$
 3. $I_T = 22 \text{ A}$





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